Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSVI)

2SK3129

Chopper Regulator, DC-DC Converter and Motor Drive Applications

• Low drain-source ON resistance: RDS (ON) = $5.5 \text{ m}\Omega$ (typ.)

• High forward transfer admittance: $|Y_{fs}| = 70 \text{ S (typ.)}$

• Low leakage current: $I_{DSS} = 100 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$

• Enhancement mode: $V_{th} = 0.8 \text{ to } 2.0 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	50	V	
Drain-gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	50	V	
Gate-source voltage		V_{GSS}	±20	V	
	DC (Note 1)	I _D	60		
Drain current	Pulse (Note 1)	I _{DP}	240	Α	
Drain power dissipation	(Tc = 25°C)	P_{D}	150	W	
Single pulse avalanche energy (Note 2)		E _{AS}	721	mJ	
Avalanche current		I _{AR}	60	Α	
Repetitive avalanche en	ergy (Note 3)	E _{AR}	12	mJ	
Channel temperature	_	T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

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Weight: 4.6 g (typ.)

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Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	0.833	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	50	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD} = 25 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), $L = 246 \,\mu\text{H}$, $R_G = 25 \,\Omega$, $I_{AR} = 60 \,\text{A}$

Note 3: Repetitive rating: pulse width limited by maximum junction temperature.

This transistor is an electrostatic-sensitive device. Please handle with caution.



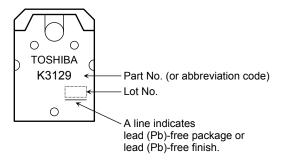
Electrical Characteristics (Ta = 25°C)

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cur	rent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	_	_	±10	μΑ
Drain cut-off curre	ent	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	_	_	100	μΑ
Drain-source brea	akdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	50	_	_	V
Gate threshold vo	oltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	0.8	_	2.0	V
Drain-source ON	resistance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 30 A	_	5.5	7	mΩ
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 30 A	40	70	_	S
Input capacitance	e	C _{iss}		_	3700	_	pF
Reverse transfer	Reverse transfer capacitance		V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	650	_	pF
Output capacitance		Coss		_	1800	_	pF
Switching time Fal	Rise time	t _r	10 V VGS 0 V 1D = 30 A C E 80 0 VDD ≈ 25 V Duty ≤ 1%, t _W = 10 μs	_	20	_	
	Turn-on time	t _{on}		_	35	_	no
	Fall time	t _f		_	160	_	ns
	Turn-off time	t _{off}		_	480	_	
Total gate charge (gate-source plus gate-drain)		Qg	V _{DD} ≈ 40 V, V _{GS} = 10 V, I _D = 60 A	_	135	_	nC
Gate-source charge		Q _{gs}		_	90	_	nC
Gate-drain ("miller") charge		Q _{gd}		_	45	_	nC

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse curre	ent (Note 1)	I _{DR}	-	_	_	60	Α
Pulse drain reverse current (Note 1)	I _{DRP}		_	_	240	Α
Forward voltage (diode)		V_{DSF}	$I_{DR} = 60 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	-1.4	V
Reverse recovery time		t _{rr}	$I_{DR} = 60 \text{ A}, V_{GS} = 0 \text{ V}$	_	180	_	ns
Reverse recovery charge		Q _{rr}	$dI_{DR}/dt = 50 A/\mu s$	-	0.32	_	μC

Marking



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20070701-EN

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